


INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)	Attorney Docket No.: 8074-1061	Application No.: NEW 10/85 415 NATIONAL PHASE
	Applicant: Yasuhiro OKAMOTO et al.	
	Filing Date: July 7, 2005	Group Art Unit:

U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No
VM	JP 2000-286428	10/13/2000	JAPAN				
	JP 11-176839	7/2/1999	JAPAN				
	JP 2002-359256	12/13/2002	JAPAN				
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

✓	U. K. MISHRA et al., "AlGaIn/GaN HEMTs-An Overview of Device Operation and Applications", Proceedings of the IEEE, Vol. 90, No. 6, June 2002
✓	J. LI et al., "High breakdown voltage GaN HFET with field plate", ELECTRONICS LETTERS, 1 st February 2001, Vol. 37, No. 3
✓	Y. ANDO et al., "A 110-W AlGaIn/GaN HETEROJUNCTION FET ON THINNED SAPPHIRE SUBSTRATE"

EXAMINER: Victor Mandala/	DATE CONSIDERED 03/27/2007
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

* English language abstract provided for the Examiner's convenience